

1       5. (Amended) A thin film transistor including:  
2              a back channel electrode,  
3              wherein a voltage of a front channel positioned on the side of a gate wiring of said  
4              thin film transistor is made equal to a voltage of said back channel positioned on the side of a  
5              back channel electrode by short-circuiting said back channel electrode to a gate electrode  
6              through a contact-hole provided in a portion of a semiconductor layer forming said thin film  
7              transistor, and  
8              wherein a passivation film patterned to have a width equal to that of said back channel  
9              electrode and said semiconductor layer are provided between said back channel and a gate  
10             insulating film.

1       15. (Amended) A thin film transistor including:  
2              a back channel electrode,  
3              wherein a voltage of a front channel positioned on the side of a gate wiring of said  
4              thin film transistor is made equal to a voltage of said back channel positioned on the side of a  
5              back channel electrode by short-circuiting said back channel electrode to a gate electrode  
6              through a contact-hole provided in a portion of a semiconductor layer forming said thin film  
7              transistor, and  
8              wherein said layer patterned to have a width equal to that of source and drain  
9              electrodes of said thin film transistor is provided between said source and drain electrodes  
10             and a gate insulating film of said film transistor.

1       16. (Amended) A thin film transistor including:  
2              a back channel electrode,  
3              wherein a voltage of a front channel positioned on the side of a gate wiring of said  
4              thin film transistor is made equal to a voltage of said back channel positioned on the side of a  
5              back channel electrode by short-circuiting said back channel electrode to a gate electrode  
6              through a contact-hole provided in a portion of a semiconductor layer forming said thin film  
7              transistor, and  
8              wherein said layer has an ohmic contact layer on the side thereof, which is in contact  
9              with source and drain electrodes of said film transistor.